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PATENT APPLICATION
Docket No.: 45688-00002
Client Ref.: US-2298-WLJ

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of: 45688-00002

For: FLIP-CHIP LIGHT-EMITTING DEVICE

CERTIFICATE OF MAILING BY EXPRESS MAIL "EXPRESS MAIL" Mailing Label No. EL374965120US Date of Deposit: November <u>4</u> , 1999 I hereby certify that the paper(s) and/or fee(s) listed below are attached hereto and are being deposited with the U.S. Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to the Assistant Commissioner of Patents, Washington, D.C. 20231 Type or Print Name: CAROL YOUNG Signature <i>Carol Young</i>
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BOX PATENT APPLICATION
Assistant Commissioner of Patents
Washington, D.C. 20231

Sir:

PATENT APPLICATION TRANSMITTAL LETTER

Transmitted herewith for filing, please find the following:

1. (XX) The specification of the above-referenced patent application is enclosed herewith (11 page(s) including claim(s) and Abstract).
2. (XX) 2 sheet(s) of:
 informal drawing(s) is (are) enclosed herewith.
 X formal drawing(s) is (are) enclosed herewith.
3. () This application is a:
 Continuation
 Divisional
 Continuation-In-Part

of prior copending parent application

Serial No. _____ filed on _____, now pending.

Please amend the application to insert the following line in the beginning of the specification:

--This application is a Continuation of prior application Serial No. _____ filed on _____, now pending.--

In the event that a petition to extend time under 37 CFR 1.136 is necessary in the parent application to maintain copendency for this application, a petition for an extension of the necessary time to maintain copendency is hereby requested for the parent application and the Commissioner is hereby authorized to debit our Account Number 10-0447 for the necessary fees.

JC678 U.S. PTO
09/434318
11/04/99

4. (X) The fees for this application have been calculated and included as shown below (Prior to calculating the fees, please enter any enclosed preliminary amendment.):

	NO. FILED	NO. EXTRA	RATE	FEE
BASIC FEE				\$760
TOTAL CLAIMS	24-20	4	\$18	72
INDEPENDENT CLAIMS	2-3	0	\$78	0
MULTIPLE DEPENDENT CLAIM(S) PRESENTED			\$260	260
TOTAL FEES:				\$1092.00
Deduct one-half of fee for Small Entity				
TOTAL AMOUNT DUE:				\$1092.00

— A check(s) in the amount of \$__ is enclosed herewith. Please charge any deficiency or credit any overpayment to Deposit Account No. _____.

— Please charge my Deposit Account No. _____ in the amount of \$_____. Please charge any deficiency or credit any overpayment to Deposit Account No. _____.

5. () An oath or declaration is enclosed herewith that is:

— Newly executed per 37 CFR 1.63(a) and (b).
 — A copy of the executed declaration filed in the prior application upon which priority is based, showing the signature or an indication thereon that it was signed; and:
 — This application is being filed fewer than all of the inventors named in the prior application and it is requested that the following name or names be deleted from the list of inventors in the prior application for this continuation or divisional application:

— The prior application was accorded status under 37 CFR § 1.47 and is accompanied by:

— A copy of the decision granting a petition to accord Sec. 1.47 status to the prior application (unless all of the inventors have or legal representatives have filed an oath or declaration to join in the prior application).
 — A copy of the subsequently executed oath(s) or declaration(s) filed by the inventor(s) or legal representative(s) that have subsequently joined in the prior application.

6. () The power of attorney for this application:
___ is appointed in the newly executed Oath or Declaration submitted herewith.
___ is appointed by the power of attorney enclosed herewith.
___ remains the same as originally in the parent application.
___ was changed during the prosecution of the parent application and a copy of the change in the power of attorney is enclosed herewith.

7. (XX) The correspondence address for this application shall be:
Stanley R. Moore, Esq.
Jenkins and Gilchrist, P.C.
3200 Fountain Place
1445 Ross Ave.
Dallas, Texas 75202
X which is a new correspondence address or a change therein.
___ which is the same as originally in the parent application.
___ which is the change in the correspondence address that was filed during the prosecution of the parent application.

8. () Priority is hereby claimed under 35 USC 119 and 172 to the following foreign applications:

Country	Serial No.	Date
_____	_____	_____
_____	_____	_____
_____	_____	_____

and:

- ___ A certified copy of each application is enclosed herewith.
___ A certified copy of each application was filed in prior application Serial No. _____.

9. () A verified statement claiming small entity status under 37 CFR 1.9 and 1.27:
___ is enclosed herewith.
___ was filed in parent application Serial No. _____, and such status remains unchanged and is requested for this application.


10. () A preliminary amendment is enclosed herewith.

11. (XX) An Information Disclosure Statement with Modified PTO Form 1449 and a copy of the cited references are enclosed herewith.

12. () An Assignment of the invention to _____ with cover sheet and recordation fee is enclosed herewith for recordation by the Assignment Branch.

13. () The Commissioner is hereby authorized to charge payment, or to credit any overpayment, of the following fees associated with this filing or during the pendency of this application to Deposit Account No. _____.
- ___ Any patent application filing fees under 37 CFR 1.16.
 - ___ Any patent application processing fees under 37 CFR 1.17.
 - ___ The issue fee under 37 CFR 1.18 at or before mailing of the Notice of Allowance, pursuant to 37 CFR 1.311(b).
14. () Other (specify): _____
15. (XX) Confirmation Postcard.

Respectfully submitted,


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65407 "BTE" 60

Flip-chip Light-emitting Device

Field of the Invention

The present invention relates to a gallium nitride (GaN)-based light-emitting device and, particularly, to a GaN-based light-emitting device having an electrode with good reflectivity of light.

Background of the Invention

GaN-based light-emitting devices are getting more attention for the reason that they can emit special frequencies of light, such as blue light and green light. The material of substrate used for GaN-based light emitting devices is limited by the property of GaN and is mainly chosen from the following material: sapphire, silicon carbide (SiC), gallium nitride (GaN), gallium phosphide (GaP) and glass. Among the above material, sapphire substrate is widely used. Since sapphire substrate is an insulator, the two electrodes of the light-emitting device must be placed on the same side of the GaN layers. It is the characteristic of so-called lateral devices. USP 5,563,422, USP 5,578,839 and USP 5,583,879 have disclosed a series of methods for manufacturing GaN-based III-V Group compound semiconductor lateral light-emitting devices using sapphire substrate. The light-emitting device manufactured therefrom is shown in Fig. 1, wherein an light-emitting diode (LED) die 10 is fixed to a lead frame 12 first, and the two electrodes 13 and 14 on the upper surface of the die 10 must be soldered with gold (or aluminium) wires 15 and 16 respectively so as to be connected to the two electrodes of the lead frame. However, the soldering pad 17 on the upper surface of the die 10 will block the light, and thus the light-emitting area is reduced and the light emitted is not uniform. In addition, in the prior light-emitting device, a light-transmitting electrode 13 is disclosed for providing the

effect of current spreading to enhance the light-emitting efficiency of the device. However, since the electrode 13 must be very thin to become light-transmitting, its lateral resistance will be great and thus its effect of current spreading will be very limited. Besides, since the electrode 13 is placed over the main light-emitting surface, even the electrode 13 is light-transmissive, it still will reduce the light-emitting efficiency of the device.

USP 4,476,620 discloses a flip-chip GaN-based light-emitting device as shown in Fig. 2, wherein the two electrodes 21 and 22 of an LED die are directly stuck on certain places of a lead frame 23. In such a flip-chip GaN-based light-emitting device, the emitted light can directly pass through the transparent substrate (such as a sapphire substrate) to the outside. There is no soldering pad in the main light-emitting surface of the flip-chip light-emitting device, and thus the light-emitting surface as well as the light-emitting efficiency will not be affected by the soldering pad. However, only about half the light emitted from the prior flip-chip GaN-based light-emitting device can directly pass through the transparent substrate to the outside. The other half of the light is directed to the electrodes (21 and 22) and the lead frame 23. Therefore, the prior device cannot achieve an effective result. Furthermore, the prior flip-chip GaN-based light-emitting device disclosed in USP 4,476,620 does not provide the current spreading effect, and thus merely the place where the electrode is located can have an effective light-emitting result while the other place cannot achieve a good light-emitting result.

In view of the above, how to substantially improve the light-emitting efficiency of a GaN-based light-emitting device is still a problem for the industry.

Summary of the Invention

The main object of the present invention is to substantially improve the light-emitting efficiency of a GaN-based light-emitting device. The light-emitting device according to the present invention is a flip-chip light-emitting device.

Therefore, there is no soldering pad in its main light-emitting surface. Additionally, the light-emitting device according to the present invention has an electrode that has good reflectivity of light and can provide effective current spreading effect. Therefore, the light directed to the electrode can be reflected by the electrode to the outside through the transparent substrate, and thus substantially increase the light-emitting efficiency of the whole device. Further, the electrode can have sufficient size and thickness to provide effective current spreading effect, such that the light-emitting diode can achieve its best light-emitting result.

A flip-chip light-emitting device according to a first embodiment of the present invention comprises a transparent substrate, a semiconductor stacked structure arranged over a main surface of the transparent substrate wherein the stacked structure comprises an n-type GaN-based III-V Group compound semiconductor layer adjacent to said main surface and a p-type GaN-based III-V Group compound semiconductor layer adjacent to the n-type semiconductor layer, a first electrode being in electrical contact with the n-type semiconductor layer, and a second electrode being in electrical contact with the p-type semiconductor layer, wherein the second electrode has good reflectivity of light and covers most of the outer surface of the p-type semiconductor layer. In an alternative embodiment of the present invention, the positions of the n-type and p-type semiconductor layers are switched, and the electrode being in contact with the n-type semiconductor layer has good reflectivity of light and covers most outer surface of the n-type semiconductor layer.

Brief Description of the Drawings

The technical content and features of the present invention will be more readily apparent from the following detailed description of the preferred embodiments with reference to the accompanying drawings in which:

Fig. 1 is a cross-sectional view illustrating a prior GaN-based light-emitting device;

Fig. 2 is a cross-sectional view illustrating a prior flip-chip GaN-based light-emitting device;

Fig. 3 is a schematic cross-sectional view illustrating a light-emitting diode according to an embodiment of the present invention;

Fig. 4 is a schematic cross-sectional view of the light-emitting diode of Fig. 3 mounted on a base in the form of flip-chip.

Detailed Description of the Preferred Embodiments

The main object of the present invention is to substantially improve the light-emitting efficiency of a GaN-based light-emitting device. The light-emitting device according to the present invention has an electrode that has good reflectivity of light and can provide effective current spreading effect. Therefore, the light directed to the electrode can be reflected by the electrode to the outside, and thus substantially increase the light-emitting efficiency of the whole device. Further, the electrode can have sufficient size and thickness to provide effective current spreading effect, so that the light-emitting diode can achieve its best light-emitting result.

Fig. 3 illustrates a light-emitting diode according to an embodiment of the present invention. The diode structure 30 comprises a transparent substrate 31 which can be made of sapphire, glass, silicon carbide (SiC), gallium nitride (GaN), gallium phosphide (GaP) or other transparent materials. A semiconductor stacked structure is arranged over a main surface of the transparent substrate 31. The stacked structure comprises an n-type GaN-based III-V Group compound semiconductor layer adjacent to said main surface and a p-type GaN-based III-V Group compound semiconductor layer adjacent to the n-type semiconductor layer. In this embodiment, the stacked structure also comprises an active layer 34

placed between the n-type GaN-based III-V Group compound semiconductor layer and the p-type GaN-based III-V Group compound semiconductor layer, while in other embodiments of the present invention, it is possible that the stacked structure does not include the active layer 34. The method for manufacturing the stacked structure is well known in the art, and thus it is unnecessary to detail it here. An electrode 35 is located in a window, that is formed by an etching process, and in electrical contact with the n-type semiconductor layer 32. An electrode 36 is arranged over most of the outer surface of the p-type semiconductor layer 33. Since there are no special limitations on the size and thickness of the electrode 36, the shape and size of the electrode 36 can be designed to achieve the best current spreading result, and thus substantially increase the light-emitting efficiency. In addition, the material of the electrode 36 is chosen to be of high reflectivity of light. Therefore, the light directed to the electrode 36 can be reflected by the electrode 36 to the direction of the transparent substrate, and thus further increase the light-emitting efficiency.

In the present invention, the electrode 36 can be of a multi-layer structure comprising a light-transmitting conductive layer and a layer of aluminium (Al) or silver (Ag). In an embodiment of the present invention, the electrode 36 can be of a nickel/gold/titanium/aluminium (Ni/Au/Ti/Al) multi-layer structure, wherein nickel/gold (Ni/Au) is formed to be a light-transmitting metal layer directly covering the p-type semiconductor layer 33, and then a titanium (Ti) layer is formed on the Ni/Au layer, and finally an aluminium (Al) layer is formed on the Ti layer. The electrode 36 is required to be of both low ohmic contact resistance and high reflectivity of light. Ni/Au is one of the materials that can be formed as a good light-transmitting ohmic contact layer for a p-type GaN-based III-V Group compound semiconductor layer. Al layer can be of good reflectivity of light. However, in a high temperature, Al and Au will diffuse into each other and destroy the reflectivity of Al. Therefore a Ti layer is used to be a diffusion barrier

between Al and Au. Ti layer itself is also of good reflectivity of light. In other embodiments of the present invention, the electrode 36 can be of a multi-layer structure of ITO/Al or ITO/Ag, wherein ITO (Indium-Tin Oxide) is formed as a light-transmitting conductive layer and the reflectivity is provided by the Al layer or Ag layer.

In the embodiment shown in Fig. 3, an insulating layer 37 can be coated on the side surface and upper surface of the diode 30 while merely exposing a portion of each electrode that is used to contact the electrode of a base. The material of the insulating layer can be SiO_x , SiN_y , etc.. The insulating layer 37 is to protect and isolate the p/n junction, to avoid short circuit caused by conductive glue and to avoid leakage.

Fig. 4 is a schematic view showing the light-emitting diode of Fig. 3 mounted on a base in the form of flip-chip. The base 40 can be a known conductive lead frame, a glass lead frame, a circuit board or a thin-film circuit. Using a conductive lead frame or a glass lead frame as the base, the final device will be a discrete light-emitting device, while using a circuit board or a thin-film circuit as the base, the light-emitting device will be in the form of surface mounted device (SMD). The base 40 has conductive portions 41 and 42 that function as a positive electrode and a negative electrode, respectively. Conductive glue 43 is applied by a machine on the positive and negative electrodes of the base 40. Then, the light-emitting diode 30 is turned over to let the transparent substrate be the top layer and the electrodes 35 and 36 face down. After determining the correct polarities of the electrodes 35 and 36, the electrodes 35 and 36 are connected to the conductive glue 43 so as to be fixed on the base and be coupled to the electrodes of the base. Finally, the conductive glue is baked in a suitable temperature during a predetermined time to complete the manufacture of the light-emitting device.

In this embodiment, about half of the light emitted from the p-n junction or the

What is claimed is:

1. A flip-chip light-emitting device, comprising
a transparent substrate;
a semiconductor stacked structure arranged over a main surface of said transparent substrate wherein said stacked structure comprises an n-type GaN-based III-V Group compound semiconductor layer adjacent to said main surface and a p-type GaN-based III-V Group compound semiconductor layer adjacent to said n-type semiconductor layer;
a first electrode being in electrical contact with said n-type semiconductor layer; and
a second electrode being in electrical contact with said p-type semiconductor layer;
wherein said second electrode has good reflectivity of light and covers most of the outer surface of said p-type semiconductor layer.
2. The device of Claim 1 wherein said stacked structure further comprises an active layer placed between said n-type semiconductor layer and said p-type semiconductor layer.
3. The device of Claims 1 or 2 further comprising an insulating layer at least coated on the side surface of the stacked structure, a portion of said first electrode and a portion of said second electrode.
4. The device of Claims 1 or 2 further comprising a base which has a first and a second conductive portions respectively connected to said first and second electrodes.
5. The device of Claim 4 wherein said base can be a conductive lead frame, a glass lead frame, a circuit board or a thin-film circuit.
6. The device of Claims 1 or 2 wherein said second electrode is a multi-layer structure comprising a light-transmitting conductive layer and a layer of aluminium (Al) or silver (Ag).

7. The device of Claims 1 or 2 wherein said second electrode is a multi-layer structure of nickel/gold/titanium/aluminium (Ni/Au/Ti/Al), Indium-Tin Oxide/aluminium (ITO/Al) or Indium-Tin Oxide/silver (ITO/Ag).
8. A flip-chip light-emitting device, comprising
a transparent substrate;
a semiconductor stacked structure arranged over a main surface of said transparent substrate wherein said stacked structure comprises an p-type GaN-based III-V Group compound semiconductor layer adjacent to said main surface and a n-type GaN-based III-V Group compound semiconductor layer adjacent to said p-type semiconductor layer;
a first electrode being in electrical contact with said n-type semiconductor layer; and
a second electrode being in electrical contact with said p-type semiconductor layer;
wherein said first electrode has good reflectivity of light and covers most of the outer surface of said n-type semiconductor layer.
9. The device of Claim 8 wherein said stacked structure further comprises an active layer placed between said n-type semiconductor layer said the p-type semiconductor layer.
10. The device of Claims 8 or 9 further comprising an insulating layer at least coated on the side surface of the stacked structure, a portion of said first electrode and a portion of said second electrode.
11. The device of Claims 8 or 9 further comprising a base which has a first and a second conductive portions respectively connected to said first and second electrodes.
12. The device of Claim 11 wherein said base can be a conductive lead frame, a glass lead frame, a circuit board or a thin-film circuit.
13. The device of Claims 8 or 9 wherein said second electrode is a multi-layer


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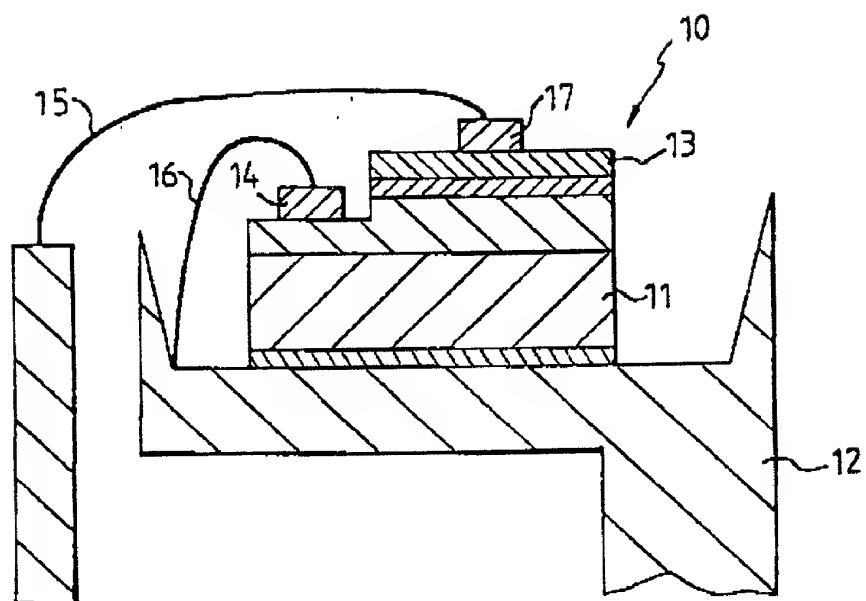


FIG. 1
(Prior Art)

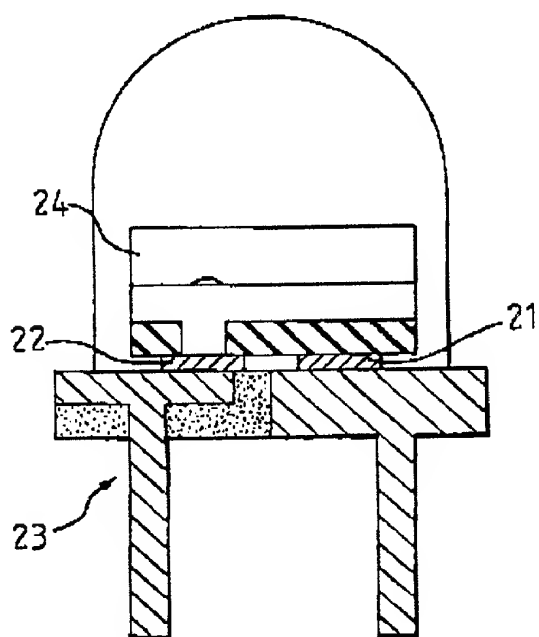


FIG. 2
(Prior Art)

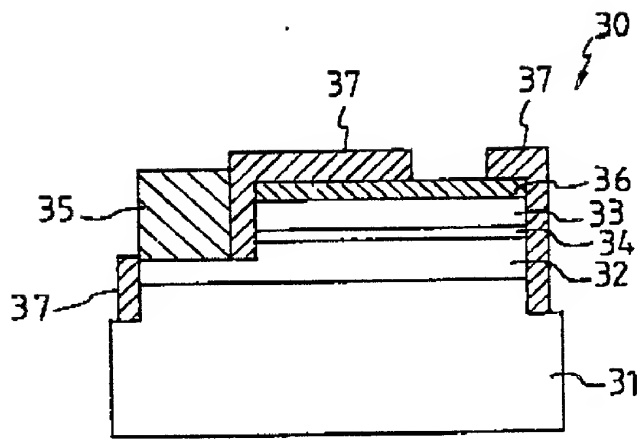


FIG. 3

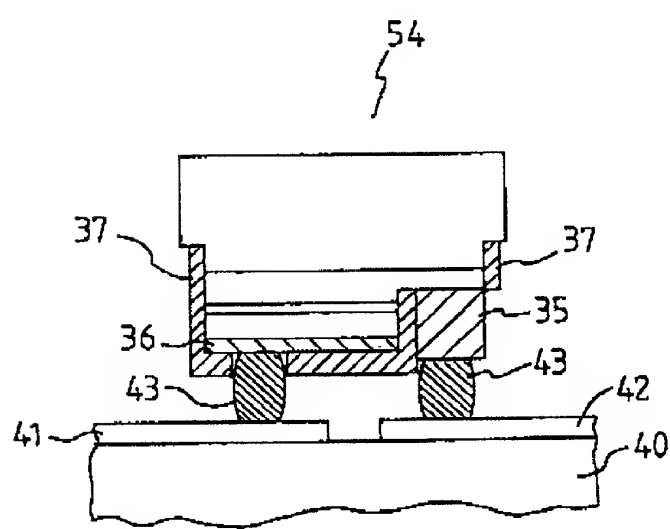


FIG. 4